# BYV36C

## SINTERED GLASS JUNCTION FAST AVALANCHE RECTIFIER E: 600V CURRENT: 1.6A

VOLTAGE: 600V







## **MECHANICAL DATA**

Case: SOD-57 sintered glass case Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C Polarity: color band denotes cathode end Mounting position: any

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	BYV36C	units
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	600	V
Maximum RMS Voltage	V <sub>RMS</sub>	420	V
Maximum DC blocking Voltage	V <sub>DC</sub>	600	V
Reverse Breakdown Voltage at IR =0. 1mA	V <sub>(BR)R</sub>	700min	V
Maximum Average Forward Rectified Current at Ttp=60°C, lead length=10mm	I <sub>F(AV)</sub>	1.6	A
Peak Forward Surge Current at t=10ms half sinewave	I <sub>FSM</sub>	30	A
$\begin{array}{ll} \mbox{Maximum Forward Voltage at rated Forward} \\ \mbox{Current and } 25^{\circ}\mbox{C} & \mbox{I}_{\rm F} = 1.0\mbox{A} \end{array}$	VF	1.35	V
Maximum DC Reverse Current $Tj = 25^{\circ}C$ at rated DC blocking voltage $Tj = 165^{\circ}C$	I <sub>R</sub>	5.0 150	μΑ μΑ
Maximum Reverse Recovery Time (Note 1)	Trr	100	nS
Non Repetitive Reverse Avalanche Energy at L=120Mh	E <sub>R</sub>	10	mJ
Typical Diode Capacitance at f=1MHz, $V_R$ =0V	Cd	45	pF
Typical Thermal Resistance (Note 2)	R <sub>th(ja)</sub>	100	K/W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175	°C

#### Note:

1. Reverse Recovery Condition  $I_F = 0.5A$ ,  $I_R = 1.0A$ ,  $I_{RR} = 0.25A$ 

2. Device mounted on an epoxy-glass printed-circuit boars, 1.5mm thick; thickness of Cu-layer  $\ge$  40  $\mu$  m

### **RATINGS AND CHARACTERISTIC CURVES BYV36C**



Fig.1 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).



Fig.3 Reverse current as a function of junction temperature; maximum values.



Fig. 5 Maximum permissible junction temperature as a function of reverse voltage.





Fig.2 Forward current as a function of forward

voltage; maximum values.



Fig.4 Diode capacitance as a function of reverse voltage, typical values.